# Cut-and-Paste Organic FET Customized ICs for Application to Artificial Skin

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# Outline

#### Introduction & motivation

# Manufacturing process

# Circuit design

# Results & discussion

#### •Summary

- Attributes of organic transistors
  - -Mechanically flexible
  - -Large area manufacturability
  - -Potentially low cost manufacturing



#### **Motivation**

- •Two driving applications of organic FETs RF ID tags and displays
- Our proposal: flexible, large-area sensors
  Organic FET + pressure sensor = artificial skin



#### **Tactile sensors for robots**

 A sensitive skin with 1,000~1M pressure sensors requires flexible, large-area switches.



Static drivers (Existing devices) Active matrix drivers (Present study)

#### **Manufacturing process**

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# **Picture of artificial skin**



# **Manufacturing process (I)**



# Manufacturing process (II)

# The device is manufactured with laminating four different sheets.



#### One sensor cell (Sencel)



#### **Sensor cell (Sencel)**



# Via holes by laser drilling machine



# **Circuit design**

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#### Concept



# Cut-and-paste feature (scalable circuit concept)

Row



#### Column selectors

# **Circuit scalability (row decoder)**



# **Circuit scalability (column selector)**



# **Connecting tape to paste**



- Connects sheet to sheet
- PET film with 0.1inch pitch Au lines
- Silver paste

# **Cut-and-paste feature (16x16 sencels)**



# **Cut-and-paste feature (convex shape)**



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#### **Cut-and-paste feature (4x4 sencels)**

![](_page_20_Picture_1.jpeg)

# Row4x4 FETdecodersmatrix

![](_page_20_Picture_3.jpeg)

#### Column selectors

#### **Results & discussion**

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![](_page_21_Picture_5.jpeg)

# **V**<sub>DS</sub>-I<sub>DS</sub> characteristics

•Match level 1 SPICE MOS model with 200k  $\Omega$ 

![](_page_22_Figure_2.jpeg)

#### Measured & simulated waveforms

![](_page_23_Figure_1.jpeg)

# **I**<sub>DS</sub> dependence on pressure

• Resistance changes between 10M  $\Omega$  (off) & 1k  $\Omega$ (on). <sub>30</sub> **V**<sub>DS</sub>=-40V V<sub>BL</sub> Access FET 20 V<sub>WL</sub> With pressure (2N) I<sub>DS</sub> [µA] Senso 10  $V_{DD}$ No pressure -40 -30 -20 -10 0 10 20  $V_{GS}$  [V]

#### **Bit-out when pressed**

#### • Pressed sencel pulls bit line up to $V_{DD}$ .

![](_page_25_Figure_2.jpeg)

# Access time dependence on $V_{\mbox{\scriptsize DD}}$

- Access time reduces to half @100V  $V_{DD}$ .
- Simulation agrees with measurement.

![](_page_26_Figure_3.jpeg)

#### **Bending test**

![](_page_27_Figure_1.jpeg)

## **Remaining issues**

- Enhancing reliability and stability
  - Current lifetime: days ———> months, years

Encapsulation

– Initial transistor yield > 99% for t<sub>insulator</sub>=500 nm

Lowering operation voltage

- Currently 40V  $\longrightarrow$  <10V

Shorter L Thinner insulator

# Summary

- An electronic artificial skin system
  - A large-area pressure sensor matrix
  - Column selectors and row decoders
  - Laser via process for circuit implementation
- Cut-and-paste customization
- Mechanical flexibility down to r=5 mm
- 23 ms delay for read-out